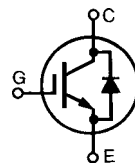


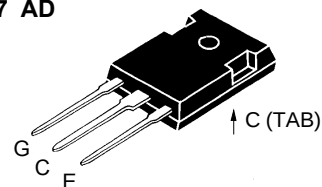
HiPerFAST™ IGBT IXGH 24N60BU1 with Diode

$$\begin{aligned} V_{CES} &= 600 \text{ V} \\ I_{C25} &= 48 \text{ A} \\ V_{CE(sat)} &= 2.3 \text{ V} \\ t_{fi} &= 80 \text{ ns} \end{aligned}$$



Symbol	Test Conditions	Maximum Ratings	
V_{CES}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}$	600	V
V_{CGR}	$T_J = 25^\circ\text{C to } 150^\circ\text{C}; R_{GE} = 1 \text{ M}\Omega$	600	V
V_{GES}	Continuous	± 20	V
V_{GEM}	Transient	± 30	V
I_{C25}	$T_C = 25^\circ\text{C}$	48	A
I_{C90}	$T_C = 90^\circ\text{C}$	24	A
I_{CM}	$T_C = 25^\circ\text{C}, 1 \text{ ms}$	96	A
SSOA (RBSOA)	$V_{GE} = 15 \text{ V}, T_{VJ} = 125^\circ\text{C}, R_G = 22 \Omega$ Clamped inductive load, $L = 100 \mu\text{H}$	$I_{CM} = 48$ @ $0.8 V_{CES}$	A
P_C	$T_C = 25^\circ\text{C}$	150	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
Maximum Lead and Tab temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		300	$^\circ\text{C}$
M_d	Mounting torque	1.13/10	Nm/lb.in.
Weight		6	g

TO-247 AD



G = Gate
E = Emitter
C = Collector
TAB = Collector

Features

- High frequency IGBT and antiparallel FRED in one package
- High current handling capability
- 3rd generation HDMOST™ process
- MOS Gate turn-on
- drive simplicity

Applications

- AC motor speed control
- DC servo and robot drives
- DC choppers
- Uninterruptible power supplies (UPS)
- Switched-mode and resonant-mode power supplies

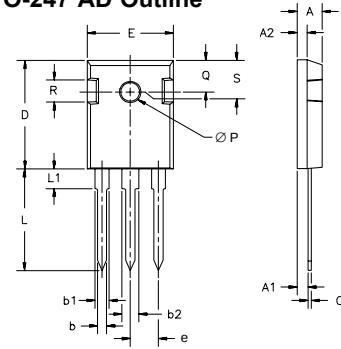
Advantages

- Space savings (two devices in one package)
- High power density
- Suitable for surface mounting
- Switching speed for high frequency applications
- Easy to mount with 1 screw (insulated mounting screw hole)

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
BV_{CES}	$I_C = 750 \mu\text{A}, V_{GE} = 0 \text{ V}$	600		V
$V_{GE(th)}$	$I_C = 250 \mu\text{A}, V_{CE} = V_{GE}$	2.5		5.5 V
I_{CES}	$V_{CE} = 0.8 \cdot V_{CES}$ $V_{GE} = 0 \text{ V}$ $T_J = 25^\circ\text{C}$ $T_J = 125^\circ\text{C}$			500 μA 8 mA
I_{GES}	$V_{CE} = 0 \text{ V}, V_{GE} = \pm 20 \text{ V}$			$\pm 100 \text{ nA}$
$V_{CE(sat)}$	$I_C = I_{C90}, V_{GE} = 15 \text{ V}$			2.3 V

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
g_{fs}	$I_C = I_{C90}, V_{CE} = 10\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$	9	13	S
C_{ies}	$V_{CE} = 25\text{ V}, V_{GE} = 0\text{ V}, f = 1\text{ MHz}$		1500	pF
C_{oes}			175	pF
C_{res}			40	pF
Q_G	$I_C = I_{C90}, V_{GE} = 15\text{ V}, V_{CE} = 0.5 V_{CES}$		90	nC
Q_{GE}			11	nC
Q_{GC}			30	nC
$t_{d(on)}$	Inductive load, $T_J = 25^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15\text{ V}, L = 100\text{ }\mu\text{H}$, $V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 10\text{ }\Omega$ Remarks: Switching times may increase for $V_{CE}(\text{Clamp}) > 0.8 \cdot V_{CES}$, 24N60BU1 higher T_J or increased R_G		25	ns
t_{ri}			15	ns
E_{on}			0.6	mJ
$t_{d(off)}$			150	ns
t_{fi}			80	ns
E_{off}			0.8	mJ
$t_{d(on)}$	Inductive load, $T_J = 125^\circ\text{C}$ $I_C = I_{C90}, V_{GE} = 15\text{ V}, L = 100\text{ }\mu\text{H}$, $V_{CE} = 0.8 V_{CES}, R_G = R_{off} = 10\text{ }\Omega$		25	ns
t_{ri}			15	ns
E_{on}			0.8	mJ
$t_{d(off)}$			250	ns
t_{fi}			100	ns
E_{off}			1.4	mJ
R_{thJC}				0.83 K/W
R_{thCK}			0.25	K/W

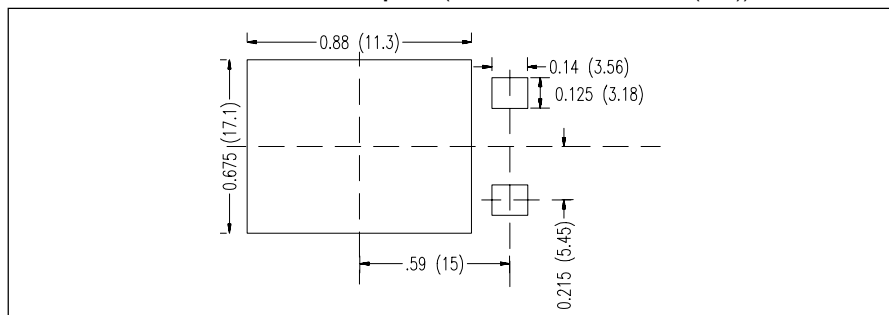
TO-247 AD Outline



Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A ₁	2.2	2.54	.087	.102
A ₂	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b ₁	1.65	2.13	.065	.084
b ₂	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L ₁		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	.242	BSC

Symbol	Test Conditions	Characteristic Values ($T_J = 25^\circ\text{C}$, unless otherwise specified)		
		min.	typ.	max.
V_F	$I_F = I_{C90}, V_{GE} = 0\text{ V}$, Pulse test, $t \leq 300\text{ }\mu\text{s}$, duty cycle $d \leq 2\%$			1.6 V
I_{RM}	$I_F = I_{C90}, V_{GE} = 0\text{ V}, -di_F/dt = 240\text{ A}/\mu\text{s}$ $V_R = 360\text{ V}$ $I_F = 1\text{ A}; -di/dt = 100\text{ A}/\mu\text{s}; V_R = 30\text{ V}$		10	A
t_{rr}			150	ns
t_{rr}			35	ns
R_{thJC}				1 K/W

Min. Recommended Footprint (Dimensions in inches and (mm))



IXYS reserves the right to change limits, test conditions, and dimensions.

IXYS MOSFETS and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,881,106	5,017,508	5,049,961	5,187,117	5,486,715	6,306,728B1
	4,850,072	4,931,844	5,034,796	5,063,307	5,237,481	5,381,025	

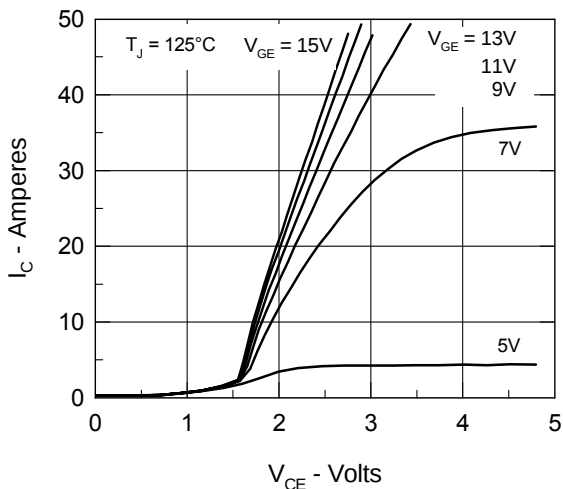


Fig. 1. Saturation Voltage Characteristics

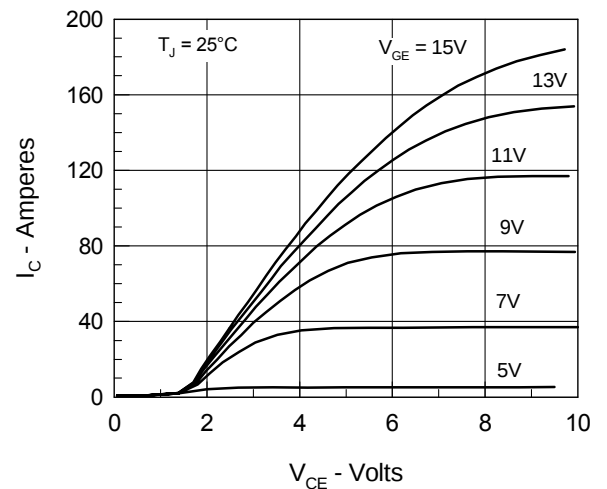


Fig. 2. Extended Output Characteristics

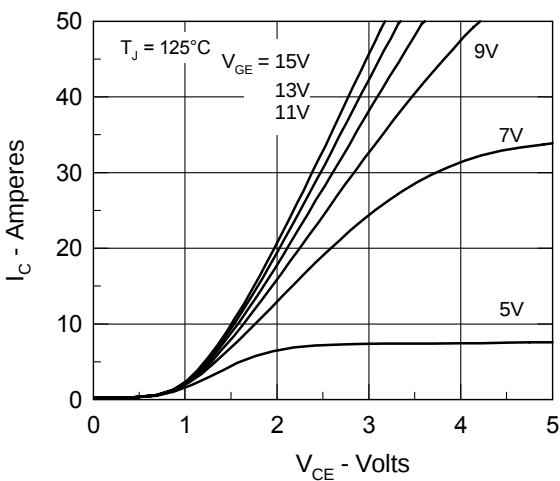


Fig. 3. Saturation Voltage Characteristics

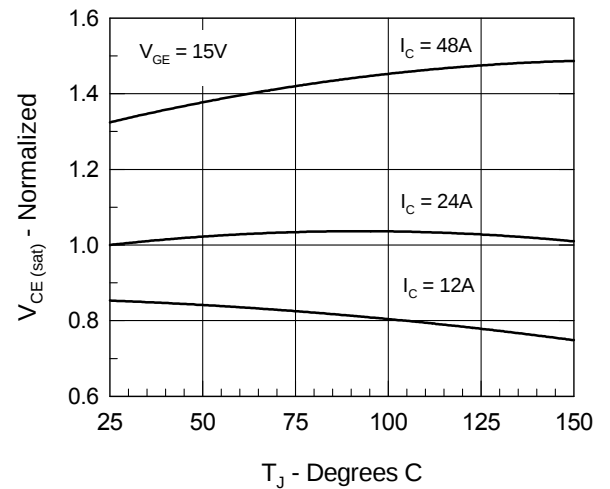
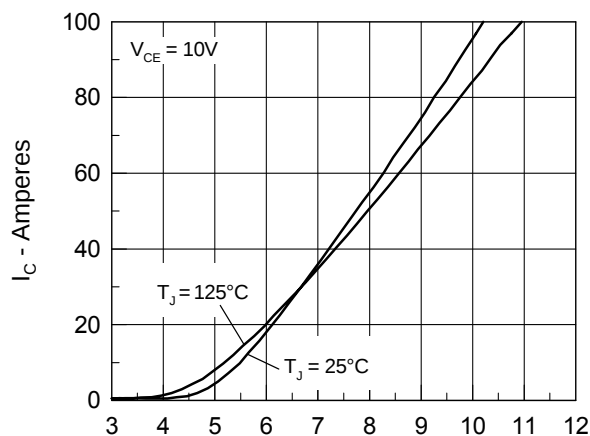
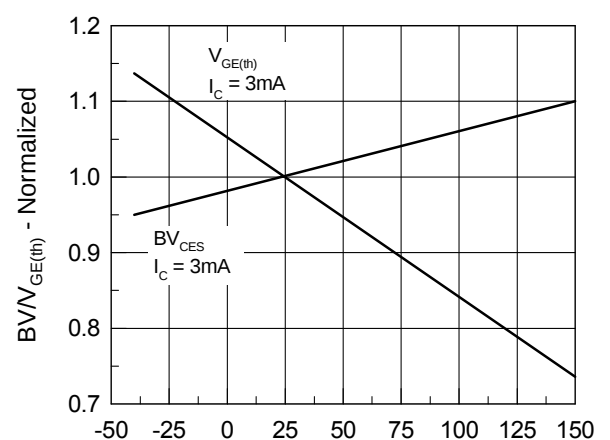
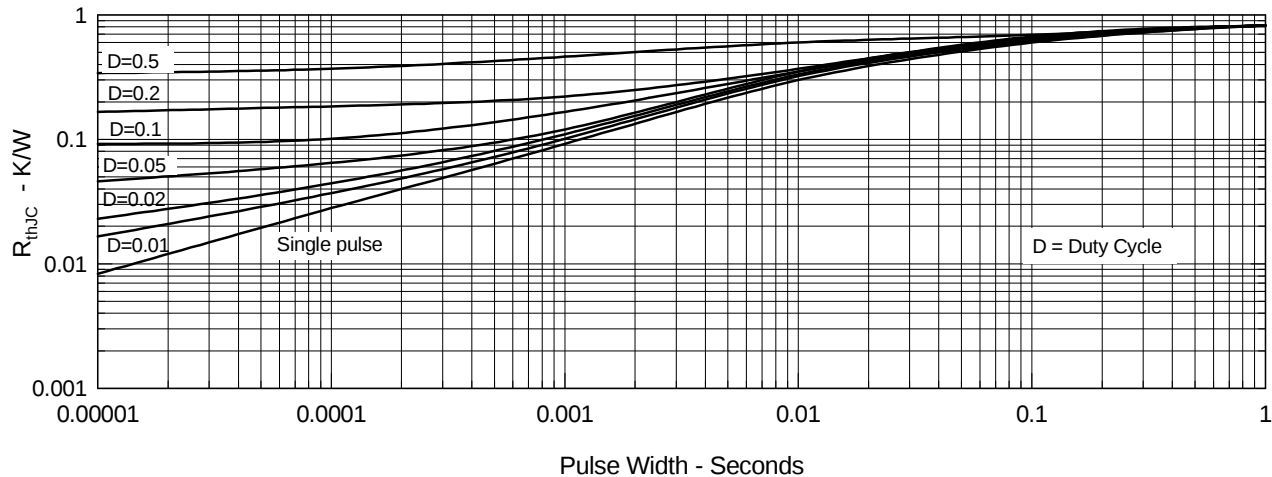
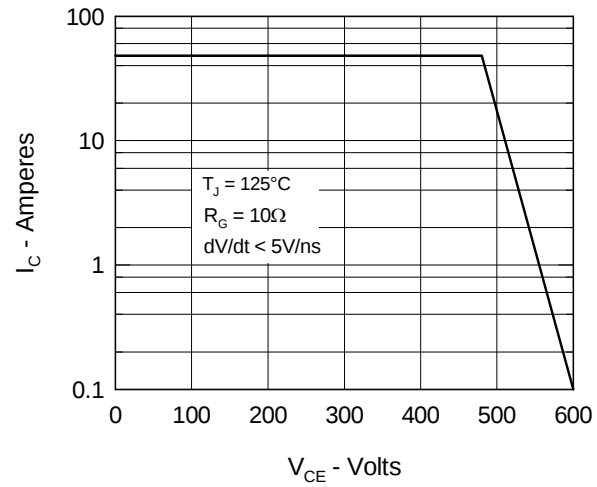
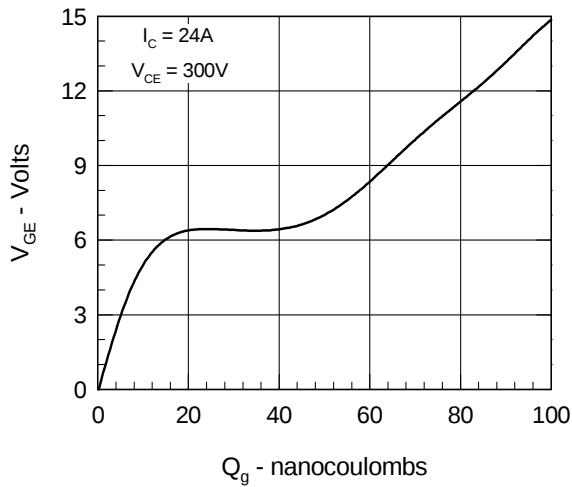
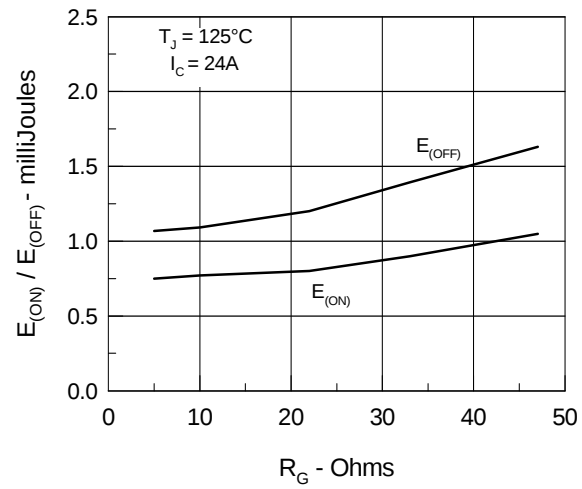
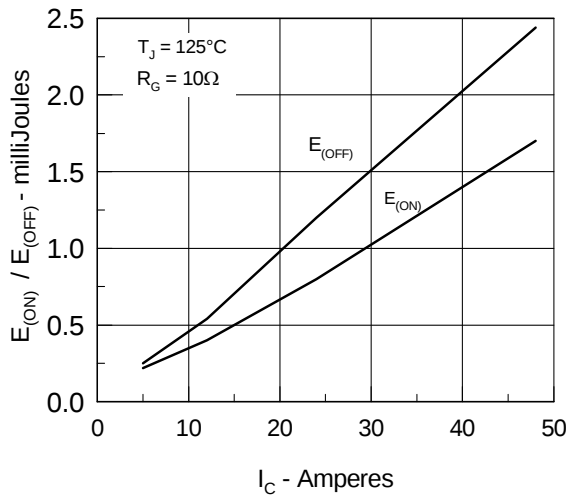

 Fig. 4. Temperature Dependence of $V_{CE(sat)}$


Fig. 5. Admittance Curves


 Fig. 6. Temperature Dependence of BV_{DSS} & $V_{GE(th)}$



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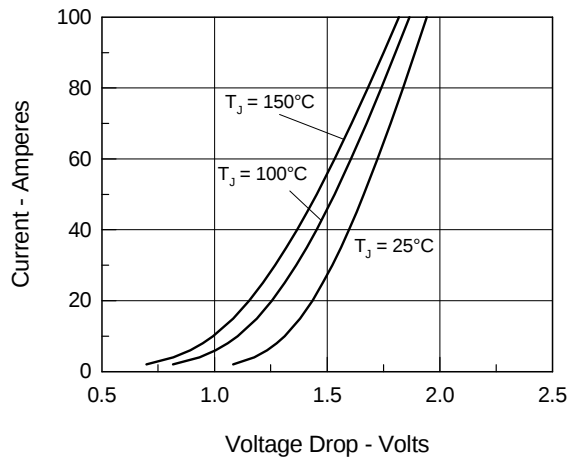


Fig.12 Maximum Forward Voltage Drop

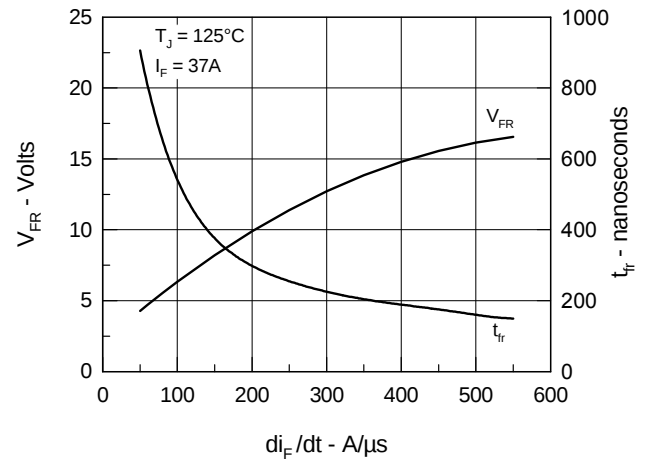


Fig.13 Peak Forward Voltage V_{FR} and Forward Recovery Time t_{FR}

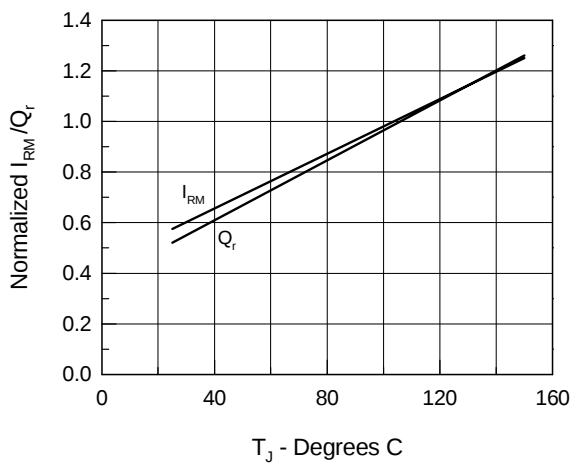


Fig.14 Junction Temperature Dependence of I_{RM} and Q_r

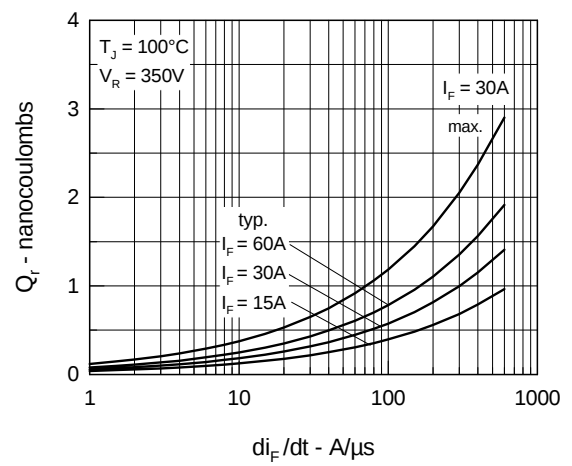


Fig.15 Reverse Recovery Charge

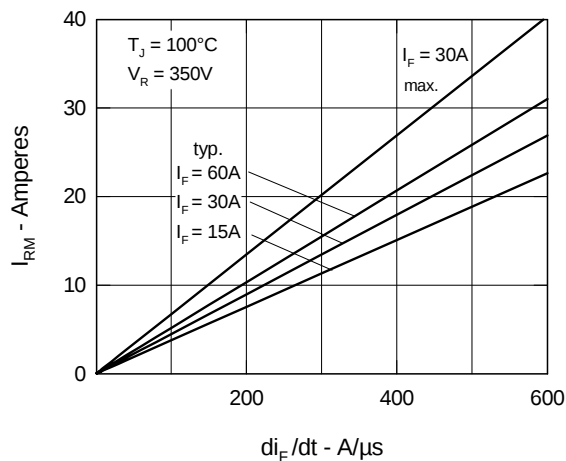


Fig.16 Peak Reverse Recovery Current

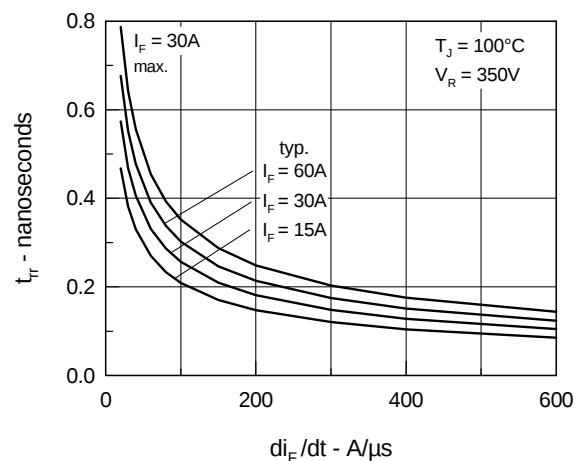


Fig.17 Reverse Recovery Time

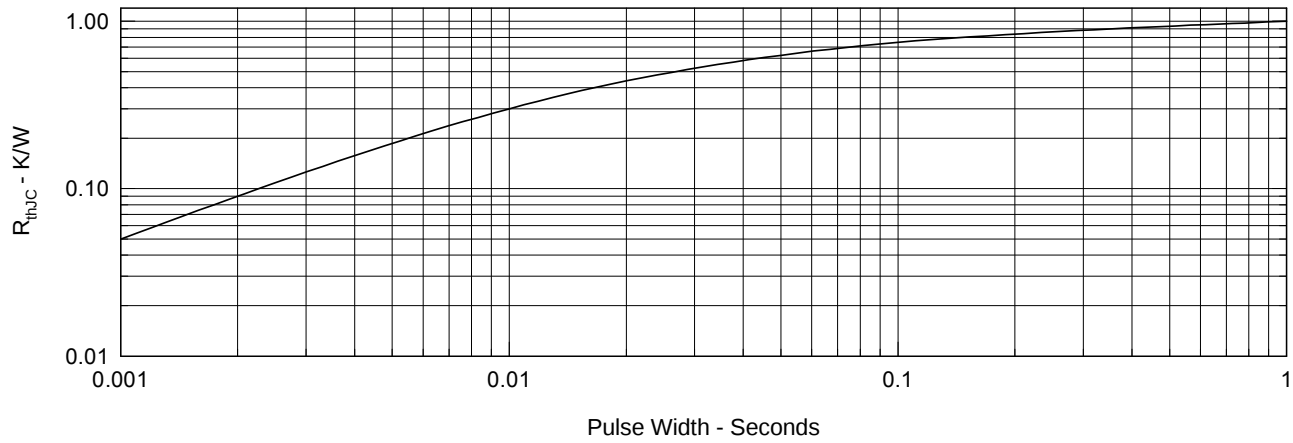


Fig.18 Diode Transient Thermal resistance junction to case